

Description

The G7P03L uses advanced trench technology to provide excellent $R_{DS(on)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a load switch or in Power management.

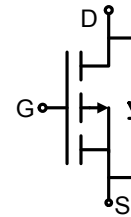
General Features

- | V_{DSS} | $R_{DS(on)}$
@ -10V (Typ) | $R_{DS(on)}$
@ -4.5V (Typ) | I_D |
|-----------|------------------------------|-------------------------------|-------|
| -30V | 19 m Ω | 23m Ω | -7A |

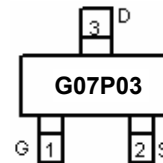
- High power and current handing capability
- RoHS Compliant
- Surface mount package

Application

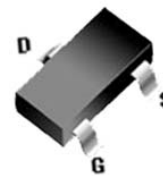
- Load switch
- Power management
- Battery Switch



Schematic diagram



Marking and Pin Assignment



SOT-23-3L

Ordering Information

Part Number	Marking	Case	Packaging
G7P03L	G7P03	SOT-23-3L	3000pcs/Reel

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	-7	A
Drain Current-Pulsed (Note 1)	I_{DM}	-21	A
Maximum Power Dissipation	P_D	1.9	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^{\circ}C$

Thermal Characteristic

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	65.7	$^{\circ}C/W$
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Electrical Characteristics (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	-30	-32	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-30V, V_{GS}=0V$	-	-	-1	μA

Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-0.5	-0.85	-1.1	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=-10V, I_D=-2A$	-	19	20.5	m Ω
		$V_{GS}=-4.5V, I_D=-2A$	-	23	26	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=-15V, I_D=-3A$	10	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{iss}	$V_{DS}=-15V, V_{GS}=0V,$ $F=1.0MHz$	-	1400	-	PF
Output Capacitance	C_{oss}		-	300	-	PF
Reverse Transfer Capacitance	C_{rss}		-	250	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=-15V, I_D=-4A$ $V_{GS}=-10V, R_{GEN}=6\Omega$	-	13	-	nS
Turn-on Rise Time	t_r		-	22	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	85	-	nS
Turn-Off Fall Time	t_f		-	72	-	nS
Total Gate Charge	Q_g	$V_{DS}=-15V, I_D=-7A$ $V_{GS}=-10V$	-	27	-	nC
Gate-Source Charge	Q_{gs}		-	5	-	nC
Gate-Drain Charge	Q_{gd}		-	7	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	$V_{GS}=0V, I_S=-3A$	-	-	-1.2	V
Diode Forward Current (Note 2)	I_S		-	-	-7	A

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

Typical Electrical And Thermal Characteristics

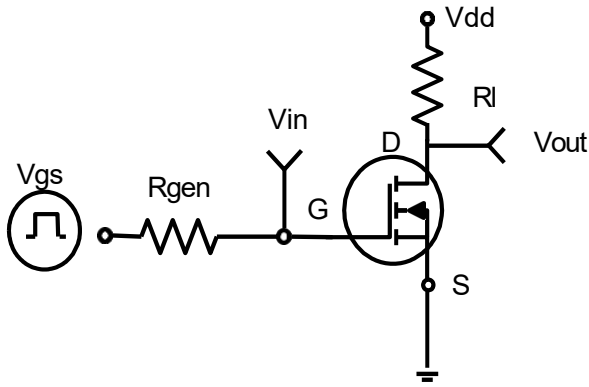


Figure 1: Switching Test Circuit

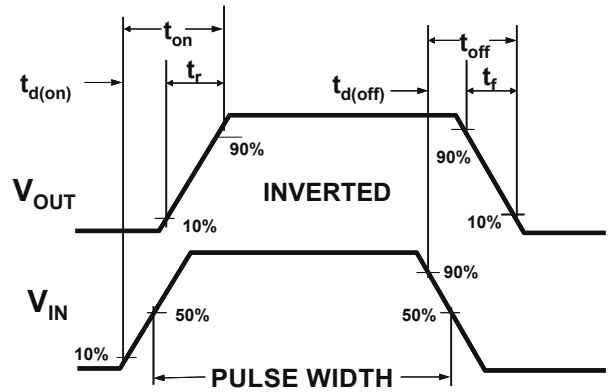


Figure 2: Switching Waveforms

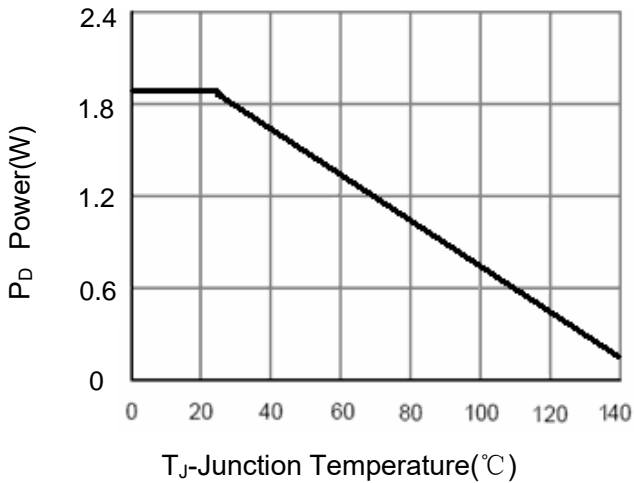


Figure 3 Power Dissipation

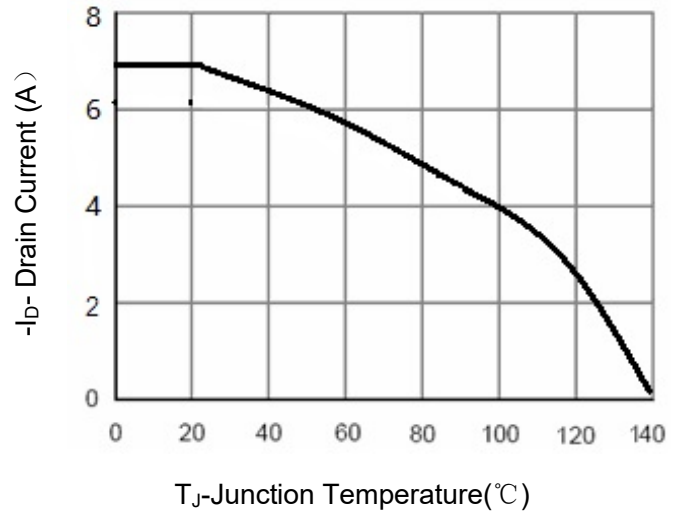


Figure 4 Drain Current

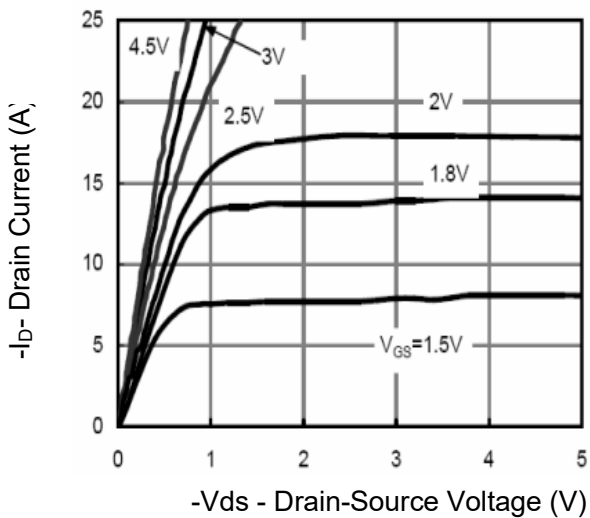


Figure 5 Output Characteristics

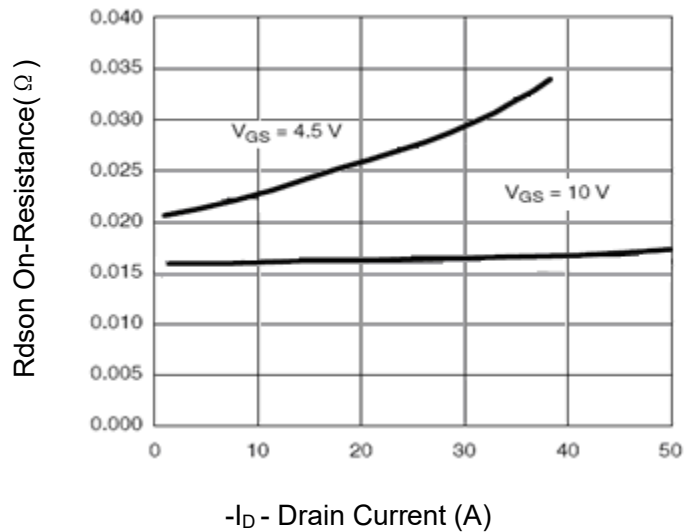


Figure 6 Drain-Source On-Resistance

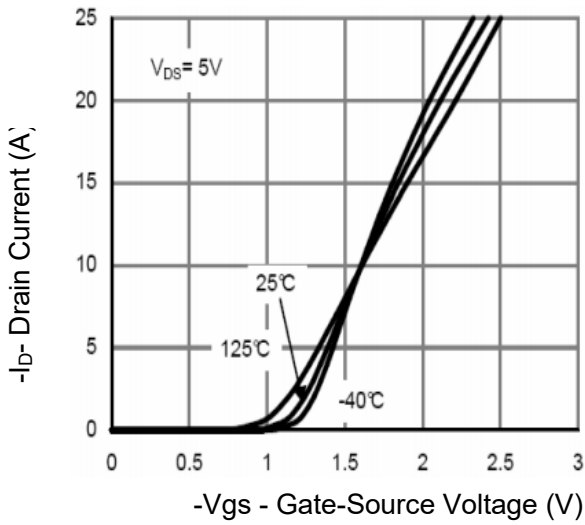


Figure 7 Transfer Characteristics

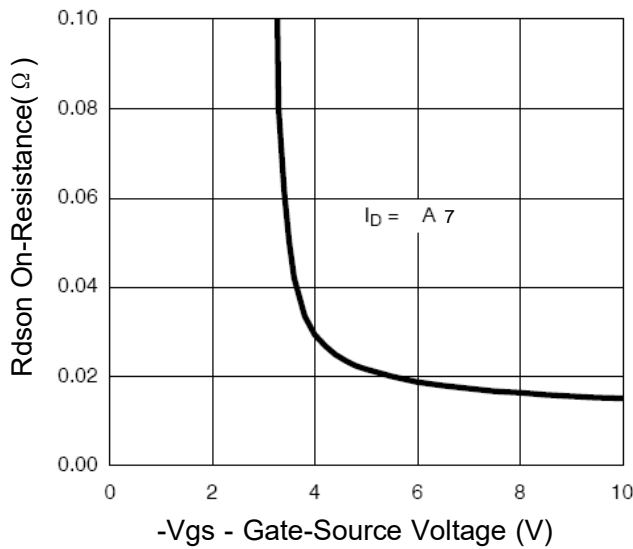


Figure 9 Rdson vs Vgs

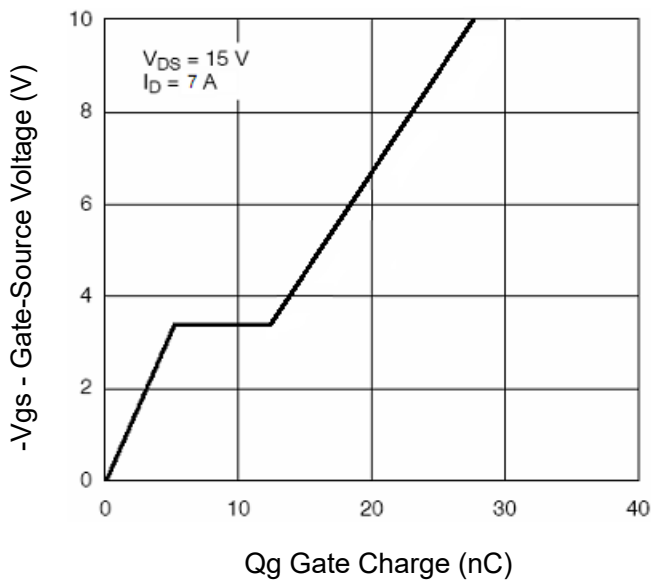


Figure 11 Gate Charge

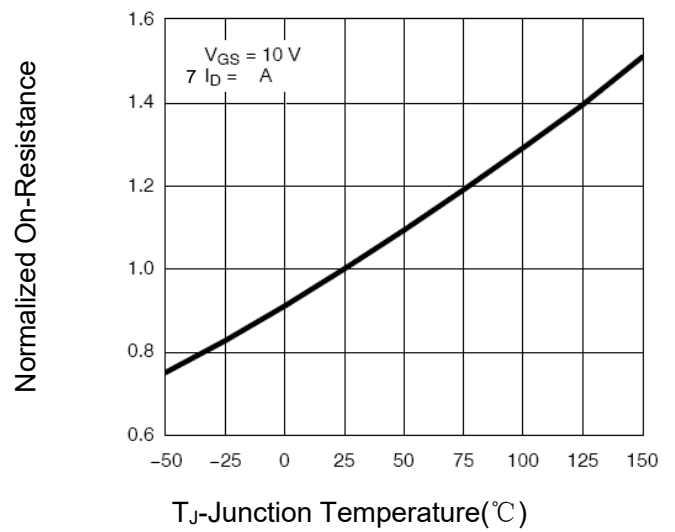


Figure 8 Drain-Source On-Resistance

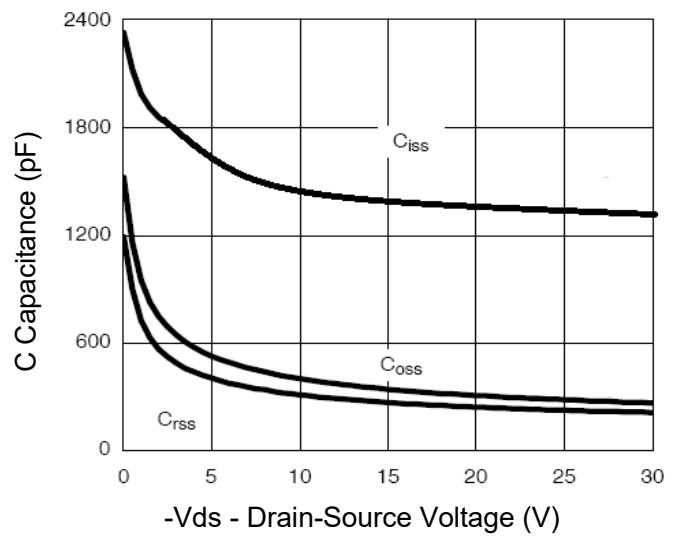


Figure 10 Capacitance vs Vds

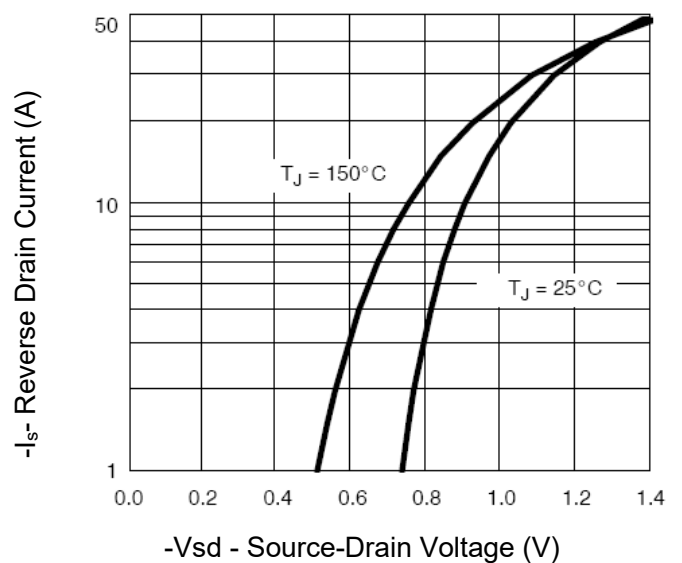


Figure 12 Source- Drain Diode Forward

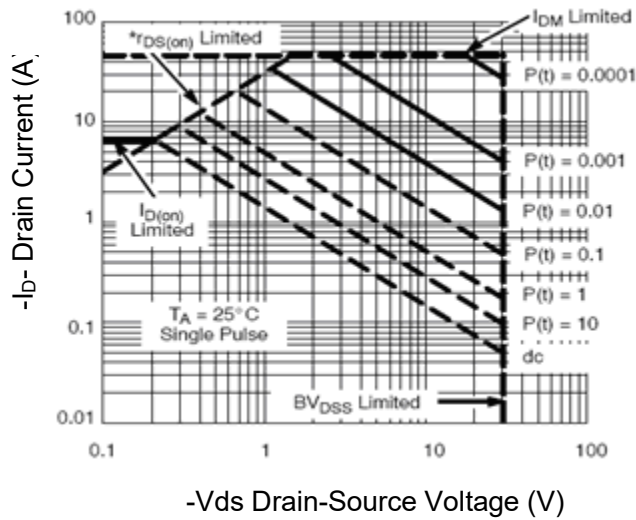


Figure 13 Safe Operation Area

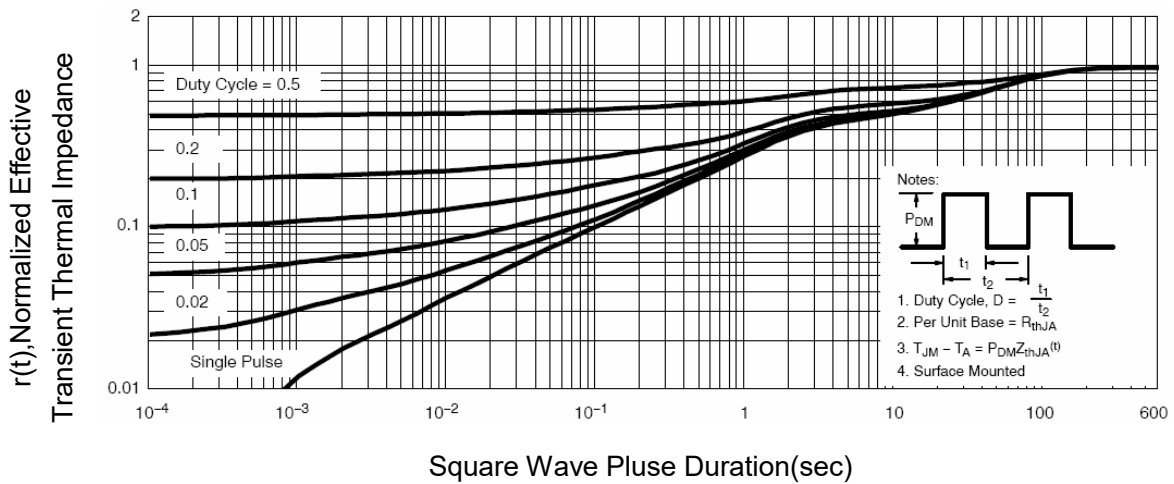
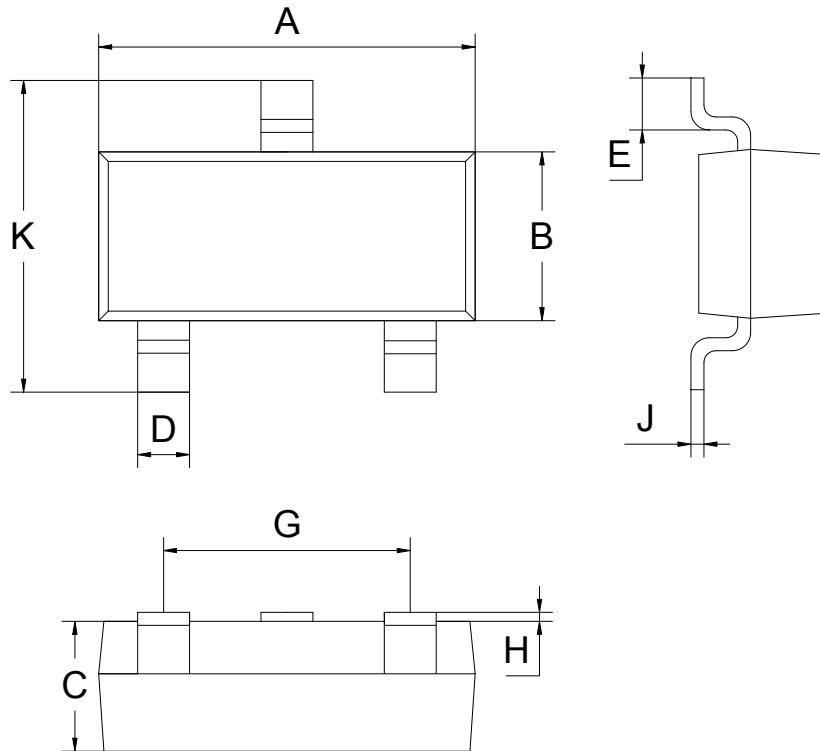


Figure 14 Normalized Maximum Transient Thermal Impedance

SOT-23-3L Package information



SOT-23-3L			
Dim	MIN	NOM	MAX
A	2.80	2.90	3.00
B	1.50	1.60	1.70
C	1.00	1.10	1.20
D	0.30	0.40	0.50
E	0.25	0.40	0.55
G	1.90		
H	0.00	-	0.10
J	0.047	0.127	0.207
K	2.60	2.80	3.00
All Dimensions in mm			